DESCRIPTION

The 2SA1162 is available in SOT-23 package.

ORDERING INFORMATION

Package Type	Part Number		
	2SA1162-O		
SOT-23	2SA1162-Y		
	2SA1162-G		
Note	SPQ: 3,000pcs/Reel		
AiT provides all RoHS Compliant Products			

HFE CLASSIFICATION

Classification	hFE
0	70~140
Υ	120~240
G	200~400

FEATURE

- Low Noise: NF=1dB (Typ.),10dB (Max).
- Complementary to 2SC2712.
- Small Package.
- Available in SOT-23 package

PIN DESCRIPTION



Pin#	Description	
1	BASE	
2	EMITTER	
3	COLLECTOR	

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified

V _{CBO} , Collector-Base Voltage	-50V
V _{CEO} , Collector-Emitter Voltage	-50V
V _{EBO} , Emitter-Base Voltage	-5V
Ic, Collector Current -Continuous	-150mA
Pc, Collector Power Dissipation	150mW
T _j , Junction Temperature	150°C
T _{stg} , Storage Temperature	-55°C ∼ + 125°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

T_a = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-50	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I_C = -1mA, I_B =0	-50	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	5	-	ı	V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-50V, I _E =0	ı	-	-0.10	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5V, I _E =0	ı	-	-0.10	μΑ
DC Current Gain	h _{FE}	V_{CE} =-6 V , I_{C} = -2 mA	70	-	400	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B = -10mA	ı	-	-0.30	V
Transition Frequency	f _T	V _{CE} =-10V, I _C =-1mA	80	-	-	MHz
Collector Base Capacitance	Cob	V _{CB} =-10V, I _E = 0, f=1MHz	-	-	7	PF
Noise Figure	NF	V_{CE} =-6V, I_{C} =0.1mA, RS=10KΩ, f=1KMHz	-	-	10	dB

TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Ic vs. VcE

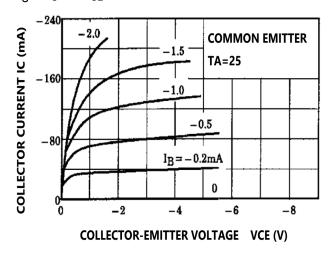


Fig 2. f_T vs. I_C

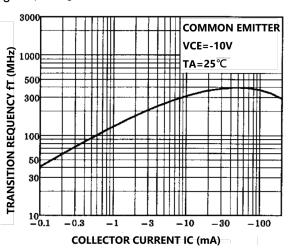


Fig 3. hfe vs. Ic

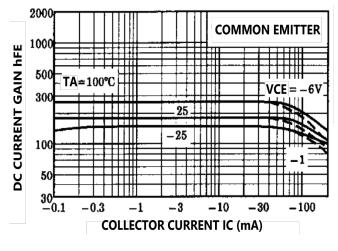


Fig 4. I_B vs. V_{BE}

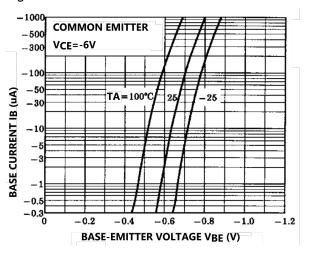


Fig 5. VcE(sat) vs. Ic

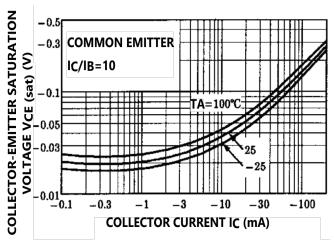
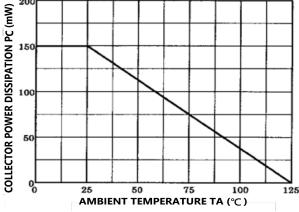


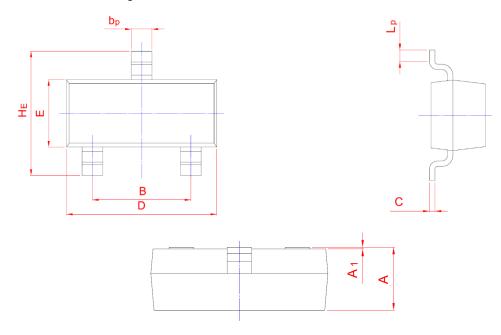
Fig 6. Pc vs. TA





PACKAGE INFORMATION

Dimension in SOT-23 Package



Comple al	Millimete	ers (mm)		
Symbol	Min.	Max.		
Α	0.950	1.400		
A1	0.100	0.013		
В	1.780	2.040		
b _p	0.340	0.500		
С	0.080	0.190		
D	2.700	3.100		
E	1.200	1.650		
HE	2.200	3.000		
L _P	0.200	0.500		



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